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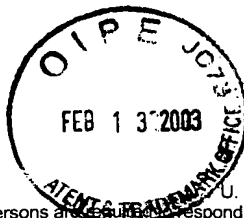
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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
				Application Number	09/853,233
				Filing Date	May 11, 2001
				First Named Inventor	Steven T. Harshfield
				Art Unit	2823
				Examiner Name	William D. Coleman
Sheet	1	of	10	Attorney Docket Number	M4065.0743/P743

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
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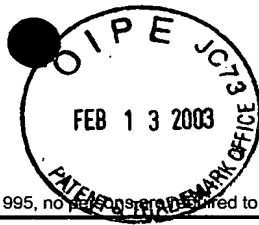
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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	BB	WO 02/21542	03/14/2002	Kozicki et al.		
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	BD	WO 97/48032	12/18/1997	Kozicki et al.		
	BE	WO 99/28914	06/10/1999	Kozicki et al.		

Examiner Signature		Date Considered	
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¹ Applicant's unique citation designation number (optional). ² See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.



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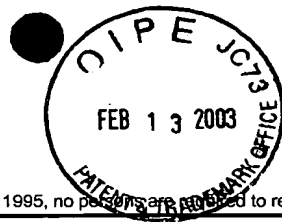
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Sheet	3	of	10		

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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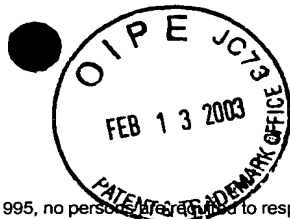
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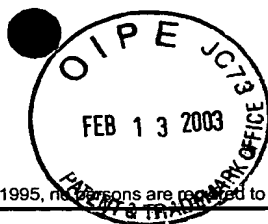
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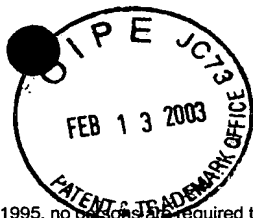
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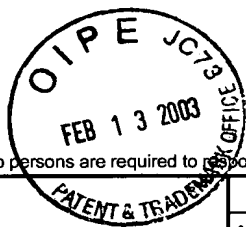
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				Group Art Unit	2823
				Examiner Name	William D. Coleman
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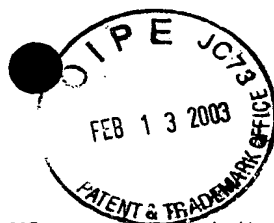
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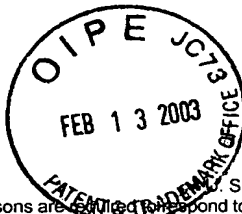
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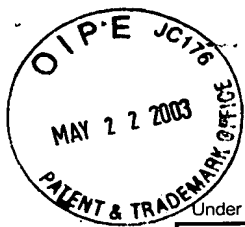
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